



STPS3045CT/CG/CP/CPI/CW

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_F(AV)$	2 x 15 A
V_{RRM}	45 V
$T_j(max)$	175 °C
V_F	0.57 V

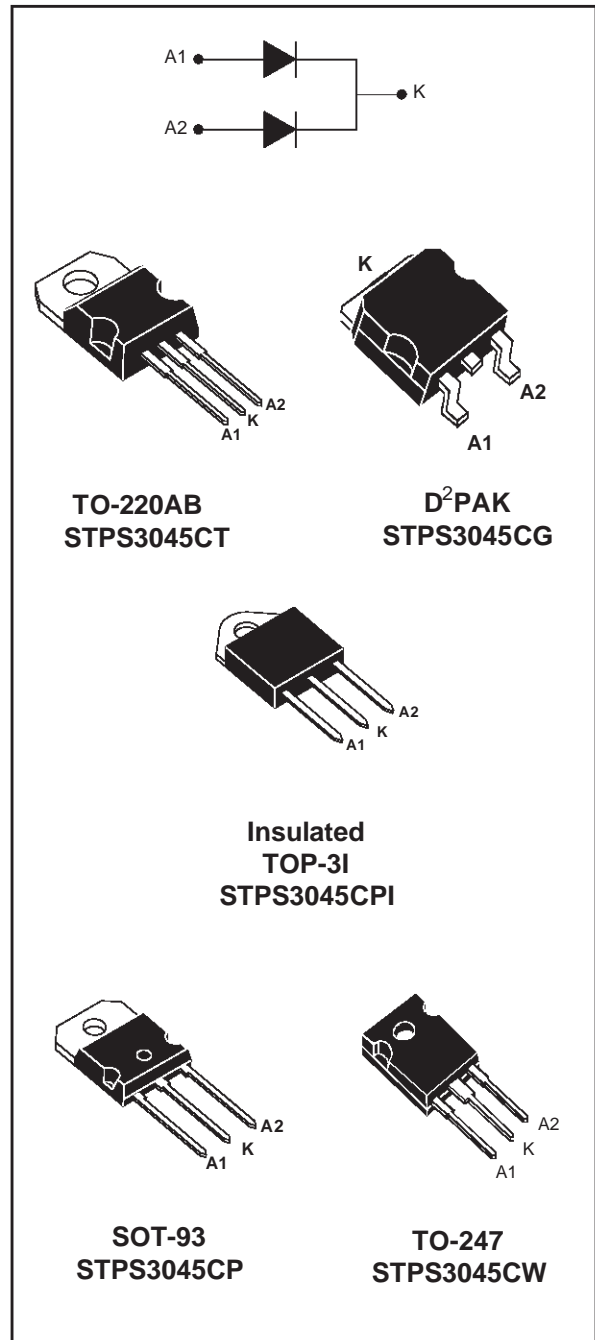
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW THERMAL RESISTANCE
- INSULATED PACKAGE: TOP-3I
Insulating voltage = 2500V RMS
Capacitance = 12pF

DESCRIPTION

Dual center tap Schottky rectifier suited for Switch-Mode Power Supply and high frequency DC to DC converters.

Packaged either in TO-220AB, D²PAK, TO-247, SOT93 or TOP-3I, this device is especially intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



STPS3045CT/CG/CP/CPI/CW

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit	
V _{RRM}	Repetitive peak reverse voltage			45	V	
I _{F(RMS)}	RMS forward current			30	A	
I _{F(AV)}	Average forward current δ = 0.5	TO-220AB D ² PAK SOT-93 TO-247	T _c = 155°C	Per diode Per device	15 30	A
		TOP-3I	T _c = 150°C			
I _{FSM}	Surge non repetitive forward current		tp = 10 ms sinusoidal	220	A	
I _{RRM}	Repetitive peak reverse current		tp = 2 μs square F = 1kHz	1	A	
I _{RSM}	Non repetitive peak reverse current		tp = 100 μs square	3	A	
T _{stg}	Storage temperature range			-65 to +175	°C	
T _j	Maximum operating junction temperature *			175	°C	
dV/dt	Critical rate of rise of reverse voltage			10000	V/μs	

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
R _{th(j-c)}	Junction to case	TO-220AB D ² PAK	Per diode Total	1.60 0.85	°C/W
		SOT-93 TO-247	Per diode Total	1.5 0.8	
		TOP-3I	Per diode Total	2.2 1.6	
R _{th(c)}		TO-220AB D ² PAK SOT-93 TO-247	Coupling	0.10	
		TOP-3I	Coupling	1.0	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode 1}) = P (\text{diode 1}) \times R_{th(j-c)} (\text{per diode}) + P (\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (Per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			200	μA
		$T_j = 125^\circ\text{C}$			11	40	mA
V_F^*	Forward voltage drop	$T_j = 125^\circ\text{C}$	$I_F = 15\text{ A}$		0.5	0.57	V
		$T_j = 25^\circ\text{C}$	$I_F = 30\text{ A}$			0.84	
		$T_j = 125^\circ\text{C}$	$I_F = 30\text{ A}$		0.65	0.72	

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :
 $P = 0.42 \times I_{F(AV)} + 0.01 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

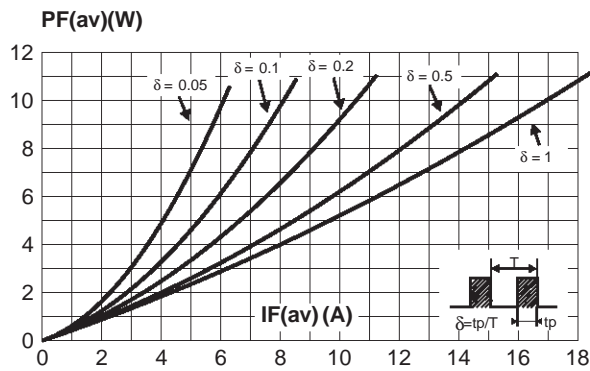


Fig. 2: Average current versus ambient temperature ($\delta = 0.5$, per diode).

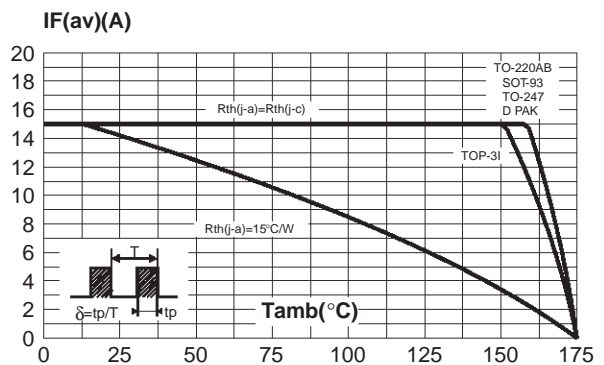


Fig. 3-1: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (TO-220AB, D²PAK, SOT-93 and TO-247).

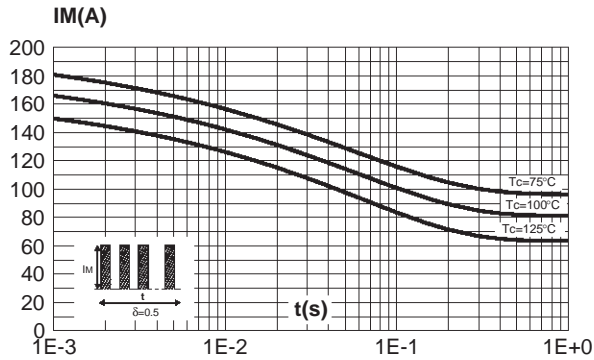


Fig. 4: Relative variation of thermal transient impedance junction to case versus pulse duration.

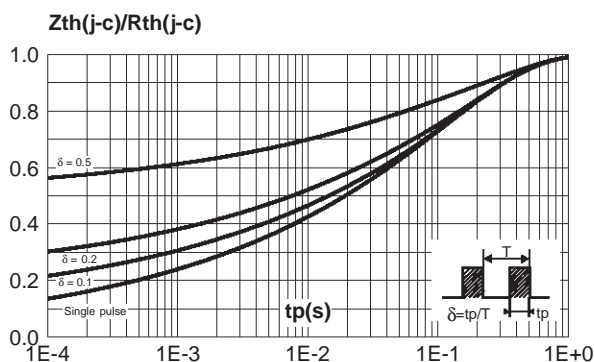


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).

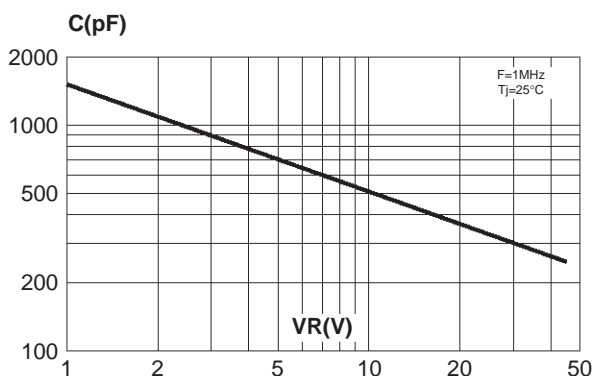


Fig. 3-2: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (TOP-3I).

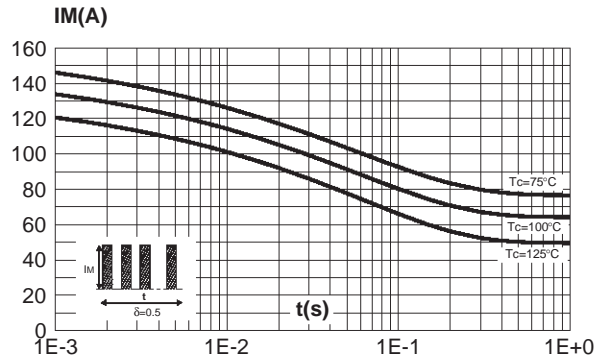


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

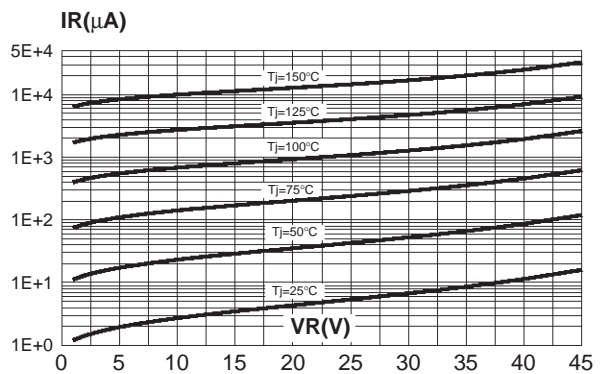
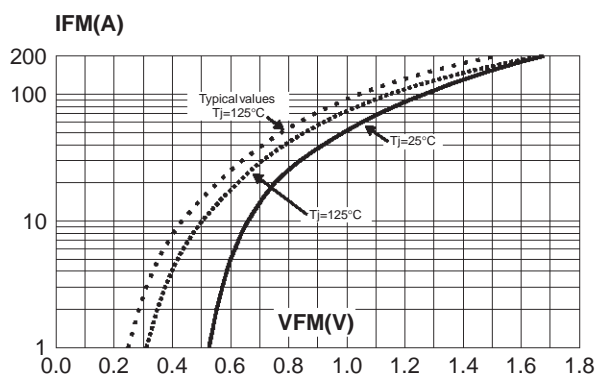
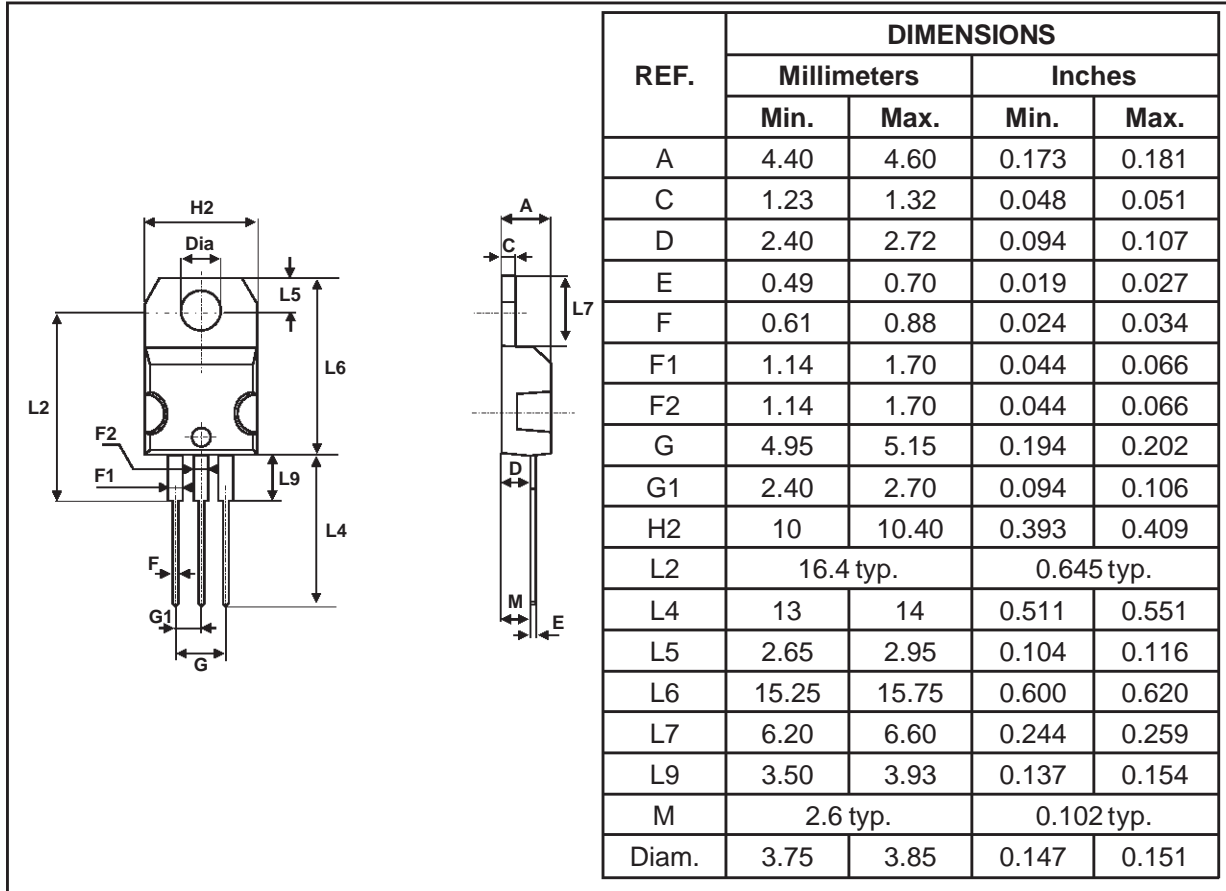


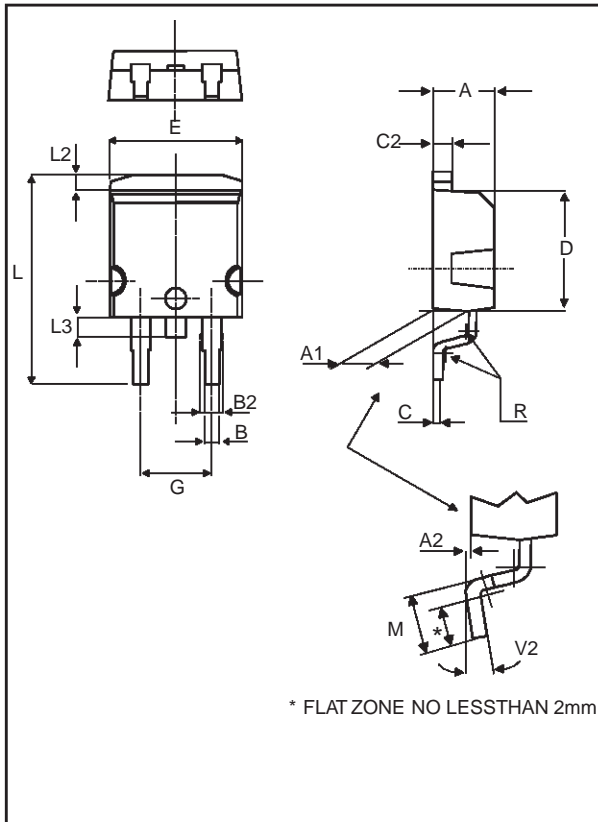
Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).



PACKAGE MECHANICAL DATA
TO-220AB

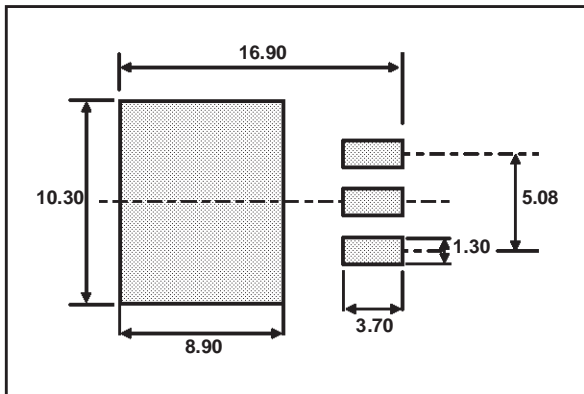


PACKAGE MECHANICAL DATA
D²PAK

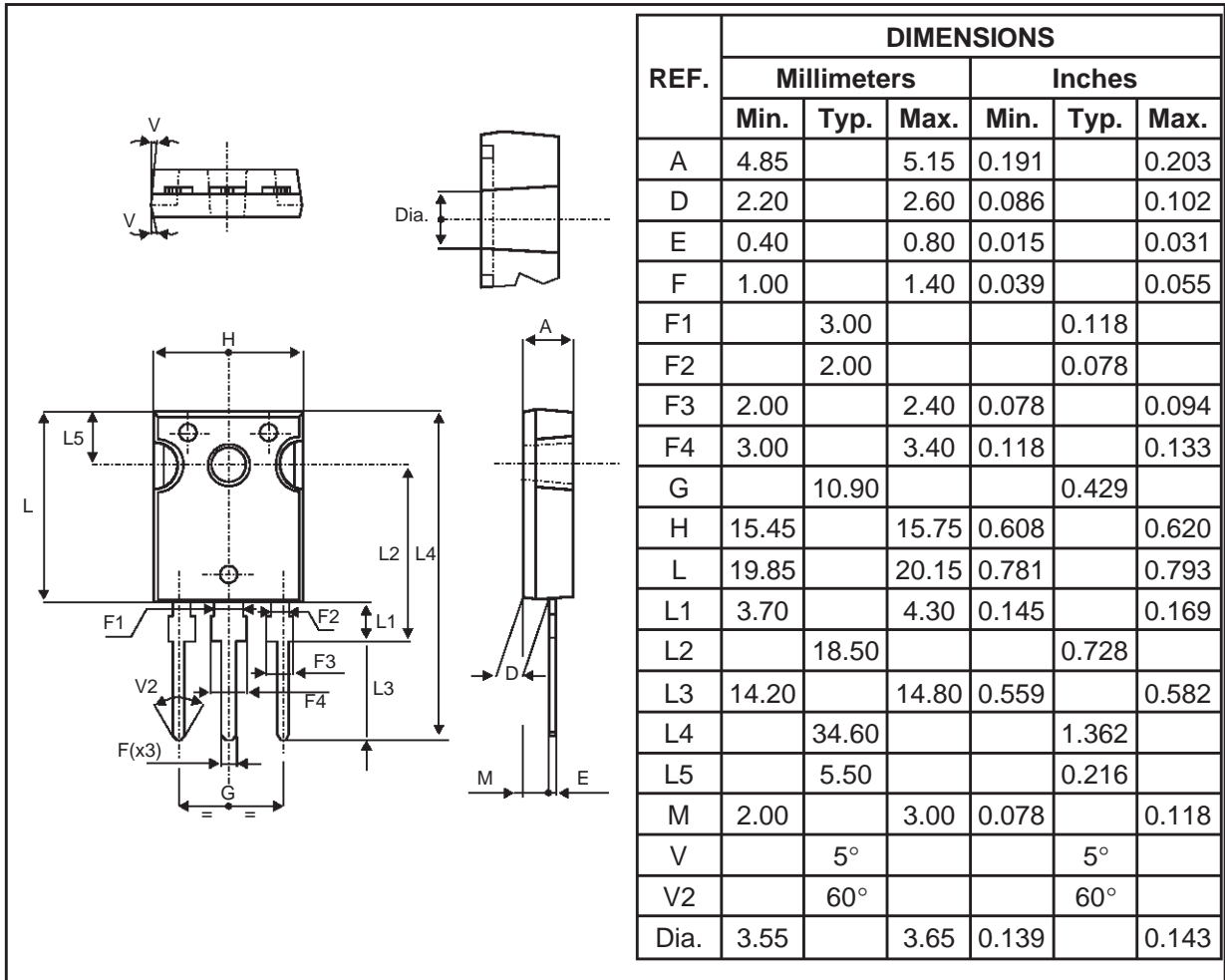


REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

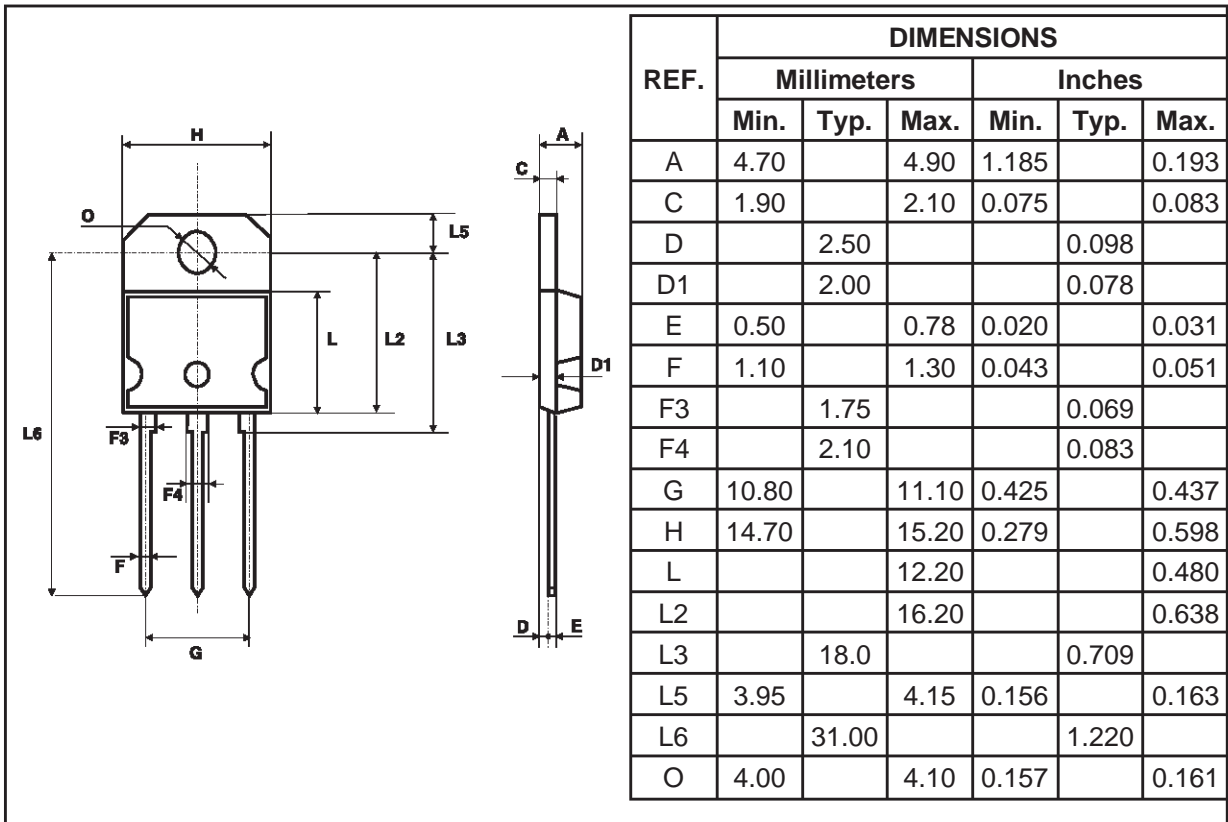
FOOTPRINT DIMENSIONS (in millimeters)



PACKAGE MECHANICAL DATA
TO-247



PACKAGE MECHANICAL DATA
SOT-93



PACKAGE MECHANICAL DATA

TOP-3I (isolated)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.5		0.7	0.020		0.028
E	2.7		2.9	0.106		0.114
F	15.8		16.5	0.622		0.650
G	20.4		21.1	0.815		0.831
H	15.1		15.5	0.594		0.610
J	5.4		5.65	0.213		0.222
K	3.4		3.65	0.134		0.144
L	4.08		4.17	0.161		0.164
P	1.20		1.40	0.047		0.055
R		4.60			0.181	

Type	Marking	Package	Weight	Base qty	Delivery mode
STPS3045CT	STPS3045CT	TO-220AB	2.23 g.	50	Tube
STPS3045CG	STPS3045CG	D ² PAK	1.48 g.	50	Tube
STPS3045CG-TR	STPS3045CG	D ² PAK	1.48 g.	1000	Tape & reel
STPS3045CP	STPS3045CP	SOT-93	3.97 g.	30	Tube
STPS3045CPI	STPS3045CPI	TOP-3I	4.46 g.	30	Tube
STPS3045CW	STPS3045CW	TO-247	4.36 g.	30	Tube

- Cooling method: by conduction (C)
- Recommended torque value (SOT-93, TOP-3I, TO-247): 0.8 N.m.
- Recommended torque value (TO-220AB): 0.55 N.m.
- Maximum torque value (SOT-93, TOP-3I, TO-247): 1.0 N.m.
- Maximum torque value (TO-220AB): 0.7 N.m.
- Epoxy meets UL94,V0

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